

Hall Ticket No

23951A1260

Course Code: AEED01



# INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous)

Dundigal, Hyderabad - 500 043

B TECH I SEMESTER CIE-II EXAMINATIONS, JANUARY - 2024

Regulation: BT23

## ELEMENTS OF ELECTRICAL AND ELECTRONICS ENGINEERING

Time: 2 Hours

(COMMON TO CSE (AI&amp;ML) | AE | ME | CE) Max Marks: 20

Answer any FOUR questions

All parts of the question must be answered in one place only

- (a) Outline the V-I characteristics of PN junction diode for forward bias and reverse bias voltages and represent the static and dynamic resistance of the diode in the characteristic curve.  
[BL: Understand | CO: 5 | Marks: 2]

(b) The reverse saturation current of a silicon PN junction diode at an operating temperature of  $27^{\circ}\text{C}$  is  $50\text{nA}$ . Compute the forward and reverse dynamic resistances of the diode for applied voltages of  $0.8\text{V}$  and  $-0.4\text{V}$  respectively.  
[BL: Apply | CO: 4 | Marks: 3]
- (a) Determine the h-parameters for the common emitter configuration using NPN transistor.  
[BL: Understand | CO: 5 | Marks: 2]

(b) Given an NPN transistor for which  $\alpha = 0.98$ ,  $I_{CO} = 2\mu\text{A}$ , and  $I_{CEO} = 16\mu\text{A}$ . A common-emitter connection is used as shown in Figure 1, with  $V_{CC} = 12\text{V}$  and  $R_C = 4\text{k}\Omega$ . What is the minimum base current required in order for the transistor to enter into saturation region?  
[BL: Apply | CO: 5 | Marks: 3]

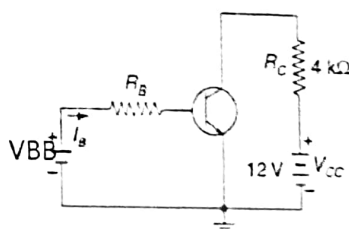


Figure 1

- (a) Illustrate the working of transistor in common collector configurations and draw its input and output characteristics.  
[BL: Understand | CO: 5 | Marks: 2]

(b) A silicon transistor with  $V_{BE} = 0.7\text{V}$ ,  $\alpha = 0.98$  and collector cut-off current of  $10\mu\text{A}$ . Assume  $R_C = 2\text{k}\Omega$ ,  $V_{CC} = 12\text{V}$  and  $I_B = 10\mu\text{A}$ . solve  $\beta$ ,  $I_{CE0}$ ,  $I_C$ ,  $I_E$  and  $V_{CE}$ .  
[BL: Apply | CO: 5 | Marks: 3]
- (a) Summarize CB, CE and CC amplifiers in terms of current gain, voltage gain, input impedance and output admittance.  
[BL: Understand | CO: 6 | Marks: 2]

(b) In a silicon transistor circuit with a fixed bias,  $V_{CC} = 12\text{V}$ ,  $R_C = 330\Omega$ ,  $I_B = 0.3\text{mA}$ ,  $\beta = 100$ ,  $V_{BE} = 0.7\text{V}$ . Solve the value of bias resistor  $R_B$  and stability factor.  
[BL: Apply | CO: 6 | Marks: 3]
- (a) Construct collector to base bias using transistor and derive the expression for stability factor.  
[BL: Understand | CO: 6 | Marks: 2]

- (b) Determine the input impedance, output impedance, voltage gain, and current-gain for the CE amplifier of Figure 2. The h-parameters of the transistor of  $h_{fe} = 60$ ,  $h_{ie} = 500 \Omega$  at  $I_C = 3$  mA. [BL: Apply | CO: 6 | Marks: 3]

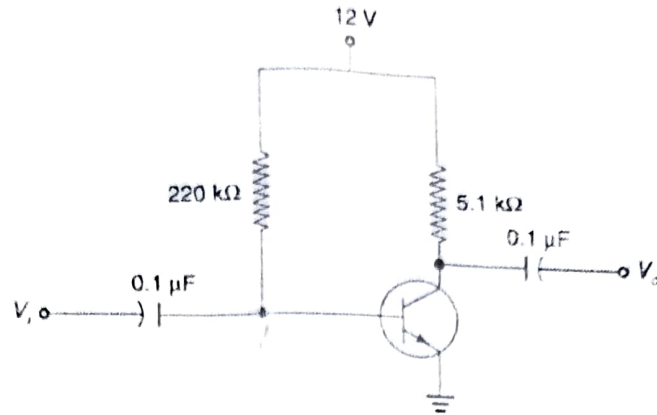


Figure 2

